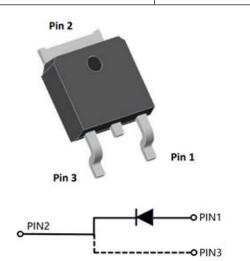


Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	16A
Qc	53nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero reverse recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-252

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112010DQG2
Reverse voltage (repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge Peak) @ T _j =25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T₀=25°C	I _F		33
Continuous forward current @ T₀=135°C		I _F	Α
Continuous forward current @ T₀=159°C			10
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	85
Power Dissipation@ T _c =25°C		- W	189
Power Dissipation@ T₀=110°C	P _{TOT}		82
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	36
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.	
		V	I _F =10A, T _j =25°C	1.42	1.54	
Forward voltage drop	V _F		I _F =10A, T _j =175°C	2.1	-	
Poverse leekage current		μА	V _R =1200V, T _j =25°C	1.3	13	
Reverse leakage current	l _R		V _R =1200V, T _j =175°C	6	-	
Total capacitive charge	Qc	nC	V_R =800V, T_j =25°C, QC = $\int_0^{VR}C(V)dV$	53		
	С			V _R =0V, f=1MHZ	700	-
Total capacitance		pF	V _R =400V, f=1MHZ	49	-	
			V _R =800V, f=1MHZ	39	-	
Capacitance Stored Energy	Ec	μJ	V _R =800V	14	-	

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	0.79

■Typical Characteristics

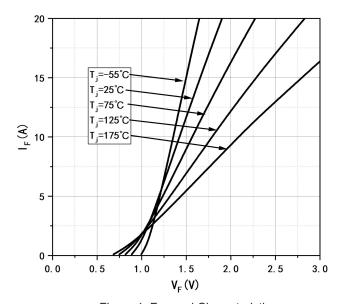


Figure 1. Forward Characteristics

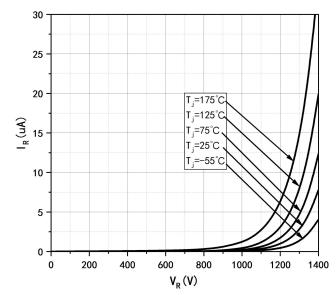
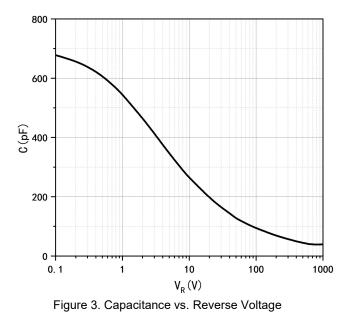


Figure 2. Reverse Characteristic







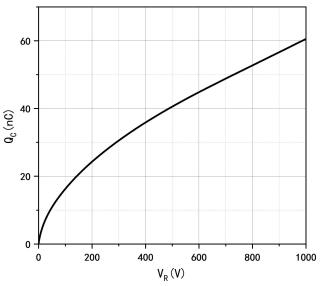


Figure 4. Total Capacitance Charge vs. Reverse Voltage

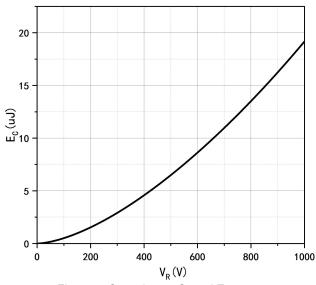
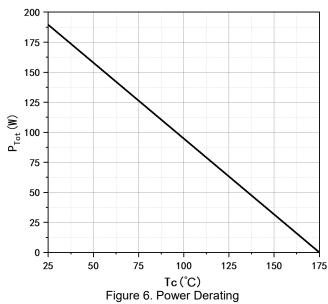
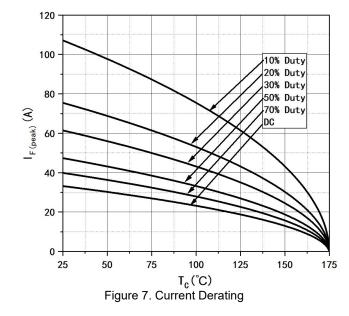


Figure 5. Capacitance Stored Energy



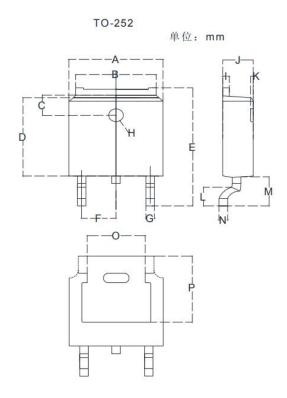


Thermal Resistance (°C/W) 0.5 0. 2 0.1 0.01 singlepulse 1E-6 1E-5 1E-4 0.001 0.01 0.1

T (Sec)
Figure 8. Transient Thermal Impedance



■Outline Dimensions



	TO-252	(5)
Dim	Min	Max
Α	6.500	6.700
В	5.100	5.460
С	1.400	1.800
D	6.000	6.200
E	10.000	10.400
F	2.166	2.366
G	0.660	0.860
Н	Ф1.050	Ф1.350
1	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
M	2.730	3.080
N	0.430	0.580
0	4.20	4.95
Р	5.15	5.45





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